

REMARKS

Applicants hereby respectfully traverse the Restriction Requirement imposed by the Examiner for the following reasons:


While the Examiner contended that "... for example in claim 1, forming the gate dielectric by depositing instead of thermally oxidizing the substrate", the Applicants respectfully submit that in order to form the device structure found in the independent device claim 19 of a bilayer gate dielectric layer including a nitrided silicon oxide material layer laminated to a non-nitrided silicon oxide material layer, the present invention method recited in the independent method Claim 1 which recites a process of "similarly oxidizing the semiconductor substrate within a thermal oxidizing atmosphere **comprising a halogen getter material** ... " must be used. Only by using the halogen getter material, such as a chlorine halogen getter material, the bilayer gate dielectric comprising nitrided and non-nitrided silicon oxide material can be formed. The restriction requirement imposed by the Examiner is therefore respectfully traversed.

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Based on the foregoing, the Applicants respectfully request the examination of device claims 19-20 together with the method claims 1-18.

Respectfully submitted,

**TUNG & ASSOCIATES**



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